



DMM Technology Corp.
Dynamic Intelligent Power Module Series

DIPM50AP600

3φ, 50A, 600V

Features

- Complete isolation between Control Side and Power Side
2000VRms insulation voltage.
- 3φ 600V 50A IGBT inverter bridge
- Direct PWM control input.
 - No external component requirements.
- Internal protection function
- Simple isolated signal interface
- High efficient switching. Low power loss.
- High DC bus voltage – up to +600VDC/High current
- Low thermal resistance
- Flat mount configuration

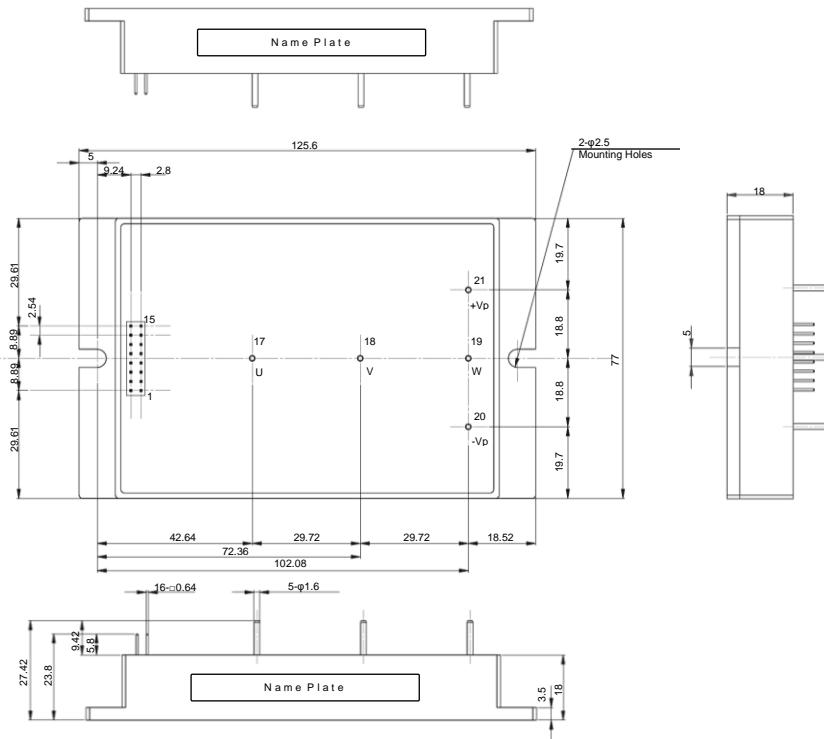


*Pre-Production Model Shown

Application

Small capacity 3-phase servo motor drive

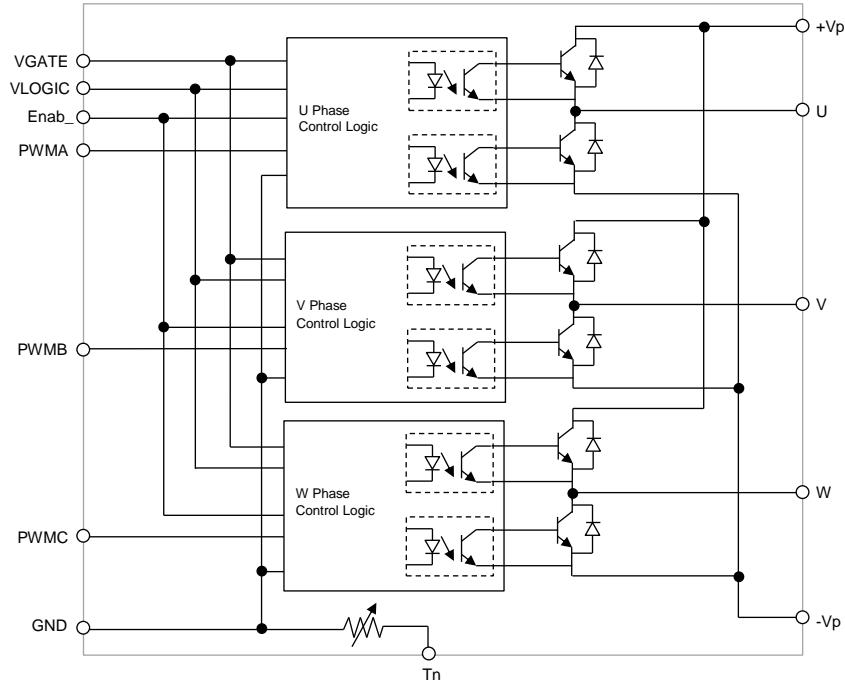
Package Outline



Terminal Configuration

Number	Name	Description
1-2	GND	Control side ground
3-4	PWMC	Control PWM for W phase
5-6	PWMB	Control PWM for V phase
7-8	PWMA	Control PWM for U phase
9-10	Enab_	Output enable, Active low
11-12	Tn	Thermal resistor output
13-14	VLOGIC	Control side +5VDC
15-16	VGATE	Control side +15VDC
17	U	Output PWM U phase
18	V	Output PWM V phase
19	W	Output PWM W phase
20	-Vp	Power side negative
21	+Vp	Power side positive

Internal Function Block Diagram



Maximum Ratings ($T_j = 25^\circ\text{C}$)

Power Side

Symbol	Parameter	Condition	Ratings	Unit
VCES	Collector - Emitter Voltage	$V_{gate} = 15\text{V}$	600	V
$\pm IC$	Collector Current	$T_c = 25^\circ\text{C}$	50	A
		$T_c = 100^\circ\text{C}$	30	A
IC Pulse	Collector Current	$T_c = 25^\circ\text{C}$	60	A
IF	Diode average forward current	$T_c = 25^\circ\text{C}$	20	A
IF Pulse	Diode forward current	$T_c = 25^\circ\text{C}$	50	A
Tj	Junction temperature		-20 ~ +150	$^\circ\text{C}$
PC	Collector dissipation	$T_c = 25^\circ\text{C}$	350	W

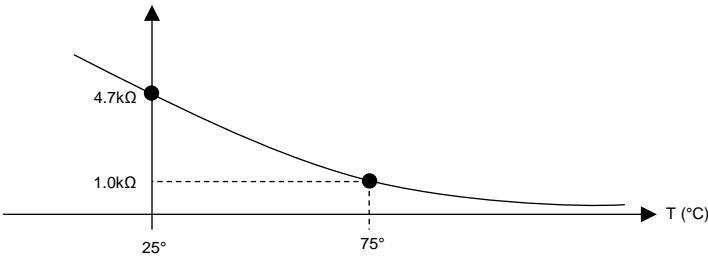
* : T_j = Junction temperature

**: T_c = Chip temperature measured under the chips

Control Side

Symbol	Parameter	Condition	Ratings	Unit
VGATE	Gate drive voltage	Applied between Vgate and GND	18	V
VLOGIC	Logic voltage	Applied between Vlogic and GND	5.25	V
PWMA PWMB PWMC Enab_	PWM and Enable Input	Applied between inputs and GND	-0.1 ~ +5.25	V

Thermal Resistance Characteristics



Symbol	Parameter	Condition	Ratings	Unit
R_{th}	Thermal Resistance	Isolated	0.6	$^\circ\text{C}/\text{W}$
$R_{(th-c)}$	Contact Thermal Resistance	Fit to external heat sink	0.24	$^\circ\text{C}/\text{W}$

Electrical Characteristics ($T = 25^\circ\text{C}$)

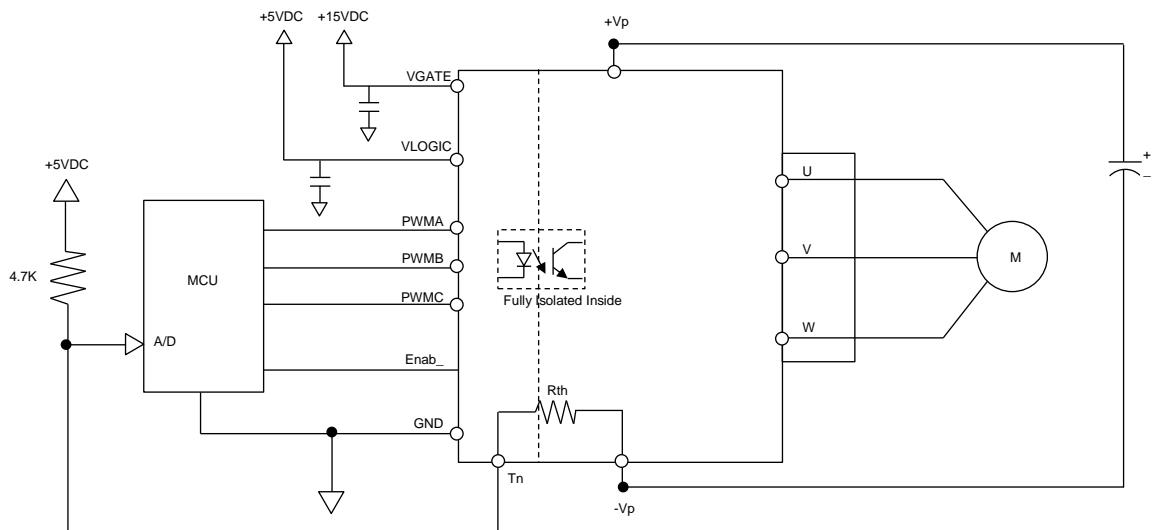
Power Side

Symbol	Parameter	Condition	Limits			Unit	
			Min.	Typical	Max.		
$V_{CE(\text{Sat})}$	Collector, Emitter Saturation Voltage	$V_{\text{gate}} = 15\text{V}$	$T_j = 25^\circ\text{C}$	—	2	2.5	V
			$T_j = 100^\circ\text{C}$	—	2.5	—	
t_{on}	Switching time		—	0.6	0.8	μs	
			—	0.6	0.8		
I_{CES}	Collector off current		$T_j = 25^\circ\text{C}$	—	—	10	mA

Control Side

Symbol	Parameter	Condition	Limits			Unit
			Min.	Typical	Max.	
V_{GATE}	Gate input voltage		12.0	15.0	18.0	V
I_{GATE}	Gate input current		—	100.0	—	mA
V_{LOGIC}	Control input voltage		4.75	5.0	5.25	V
I_{LOGIC}	Control input current		—	50.0	—	mA
Enab_- PWMA PWMB PWMC	All logic inputs	Logic high	3.0	5.0	5.25	V
		Logic low	-0.1	0.0	2.0	V

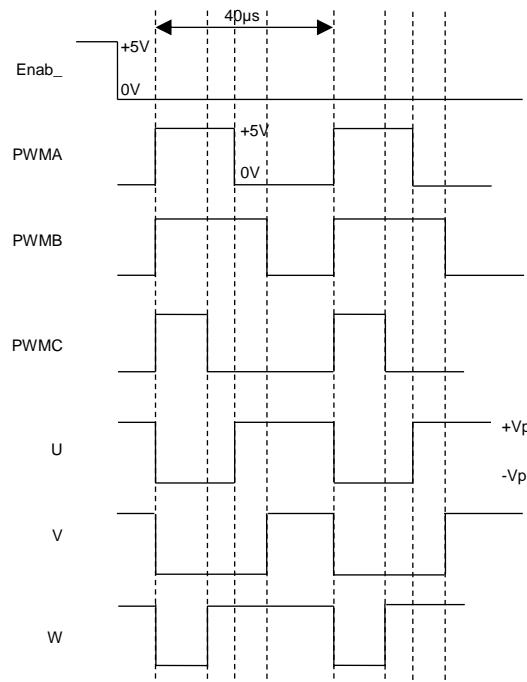
Application Circuit Example



Recommended Conditions for Use

Symbol	Parameter	Conditions	Recommended Value	Unit
VCE	Supply Voltage	Applied between +Vp and -Vp	≤ 500	V
IOUTPUT	Output Current	Current through U,V,W pins	≤ 25	A
VGATE	Gate Voltage	Applied between VGATE and GND	15	V
VLOGIC	Control Voltage	Applied between VLOGIC and GND	5	V
PWMA PWMB PWMC Enab_	Logic input levels	Applied between inputs and GND	0 or 5	V
PWM	Control input PWM	PWM input frequency	$\leq 30k$	Hz

Operating Waveform Example



Control Safety Circuit Example

